

IRLML5203PbF

HEXFET® Power MOSFET

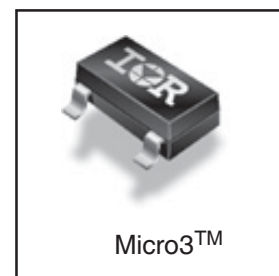
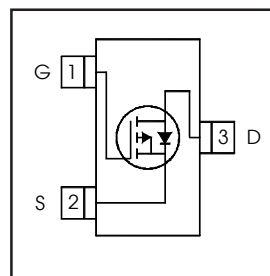
- Ultra Low On-Resistance
- P-Channel MOSFET
- Surface Mount
- Available in Tape & Reel
- Low Gate Charge
- Lead-Free

V _{DSS}	R _{DS(on)} max (mΩ)	I _D
-30V	98 @ V _{GS} = -10V	-3.0A
	165 @ V _{GS} = -4.5V	-2.6A

Description

These P-channel MOSFETs from International Rectifier utilize advanced processing techniques to achieve the extremely low on-resistance per silicon area. This benefit provides the designer with an extremely efficient device for use in battery and load management applications.

A thermally enhanced large pad leadframe has been incorporated into the standard SOT-23 package to produce a HEXFET Power MOSFET with the industry's smallest footprint. This package, dubbed the Micro3™, is ideal for applications where printed circuit board space is at a premium. The low profile (<1.1mm) of the Micro3 allows it to fit easily into extremely thin application environments such as portable electronics and PCMCIA cards. The thermal resistance and power dissipation are the best available.



Absolute Maximum Ratings

	Parameter	Max.	Units
V _{DS}	Drain- Source Voltage	-30	V
I _D @ T _A = 25°C	Continuous Drain Current, V _{GS} @ -10V	-3.0	A
I _D @ T _A = 70°C	Continuous Drain Current, V _{GS} @ -10V	-2.4	
I _{DM}	Pulsed Drain Current ①	-24	
P _D @ T _A = 25°C	Power Dissipation	1.25	W
P _D @ T _A = 70°C	Power Dissipation	0.80	
	Linear Derating Factor	10	mW/°C
V _{GS}	Gate-to-Source Voltage	± 20	V
T _J , T _{STG}	Junction and Storage Temperature Range	-55 to + 150	°C

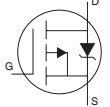
Thermal Resistance

	Parameter	Max.	Units
R _{θJA}	Maximum Junction-to-Ambient ③	100	°C/W

Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
V _{(BR)DSS}	Drain-to-Source Breakdown Voltage	-30	—	—	V	V _{GS} = 0V, I _D = -250μA
ΔV _{(BR)DSS} /ΔT _J	Breakdown Voltage Temp. Coefficient	—	0.019	—	V/°C	Reference to 25°C, I _D = -1mA
R _{DS(on)}	Static Drain-to-Source On-Resistance	—	—	98	mΩ	V _{GS} = -10V, I _D = -3.0A ②
		—	—	165		V _{GS} = -4.5V, I _D = -2.6A ②
V _{GS(th)}	Gate Threshold Voltage	-1.0	—	-2.5	V	V _{DS} = V _{GS} , I _D = -250μA
g _{fs}	Forward Transconductance	3.1	—	—	S	V _{DS} = -10V, I _D = -3.0A
I _{DSS}	Drain-to-Source Leakage Current	—	—	-1.0	μA	V _{DS} = -24V, V _{GS} = 0V
		—	—	-5.0		V _{DS} = -24V, V _{GS} = 0V, T _J = 70°C
I _{GSS}	Gate-to-Source Forward Leakage	—	—	-100	nA	V _{GS} = -20V
	Gate-to-Source Reverse Leakage	—	—	100		V _{GS} = 20V
Q _g	Total Gate Charge	—	9.5	14	nC	I _D = -3.0A
Q _{gs}	Gate-to-Source Charge	—	2.3	3.5		V _{DS} = -24V
Q _{gd}	Gate-to-Drain ("Miller") Charge	—	1.6	2.4		V _{GS} = -10V ②
t _{d(on)}	Turn-On Delay Time	—	12	—	ns	V _{DD} = -15V ②
t _r	Rise Time	—	18	—		I _D = -1.0A
t _{d(off)}	Turn-Off Delay Time	—	88	—		R _G = 6.0Ω
t _f	Fall Time	—	52	—		V _{GS} = -10V
C _{iss}	Input Capacitance	—	510	—	pF	V _{GS} = 0V
C _{oss}	Output Capacitance	—	71	—		V _{DS} = -25V
C _{rss}	Reverse Transfer Capacitance	—	43	—		f = 1.0MHz

Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I _S	Continuous Source Current (Body Diode)	—	—	-1.3	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I _{SM}	Pulsed Source Current (Body Diode) ①	—	—	-24		
V _{SD}	Diode Forward Voltage	—	—	-1.2	V	T _J = 25°C, I _S = -1.3A, V _{GS} = 0V ②
t _{rr}	Reverse Recovery Time	—	17	26	ns	T _J = 25°C, I _F = -1.3A
Q _{rr}	Reverse Recovery Charge	—	12	18	nC	di/dt = -100A/μs ②

Notes:

① Repetitive rating; pulse width limited by max. junction temperature.

② Pulse width ≤ 400μs; duty cycle ≤ 2%.

③ Surface mounted on FR-4 board, t ≤ 5sec.

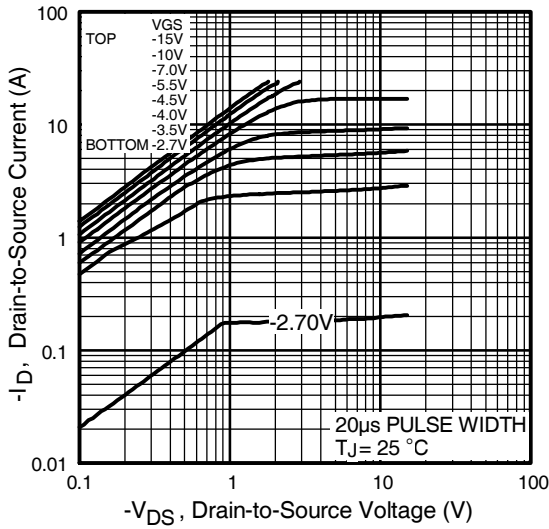


Fig 1. Typical Output Characteristics

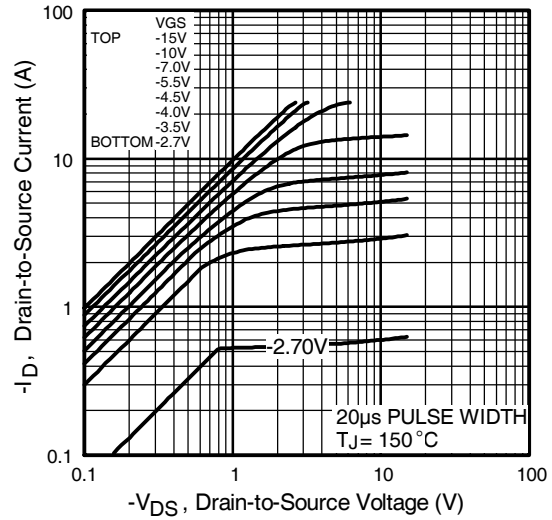


Fig 2. Typical Output Characteristics

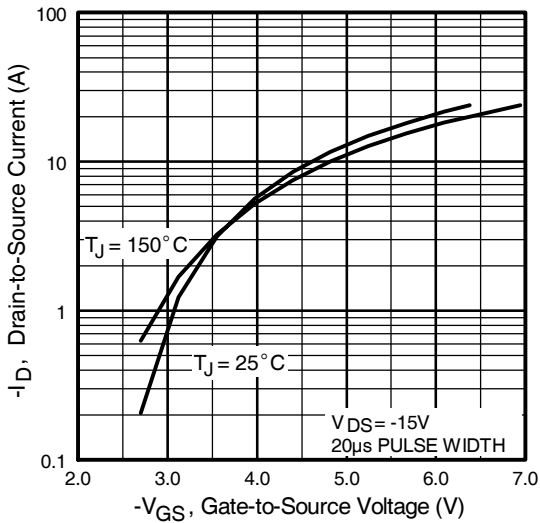


Fig 3. Typical Transfer Characteristics

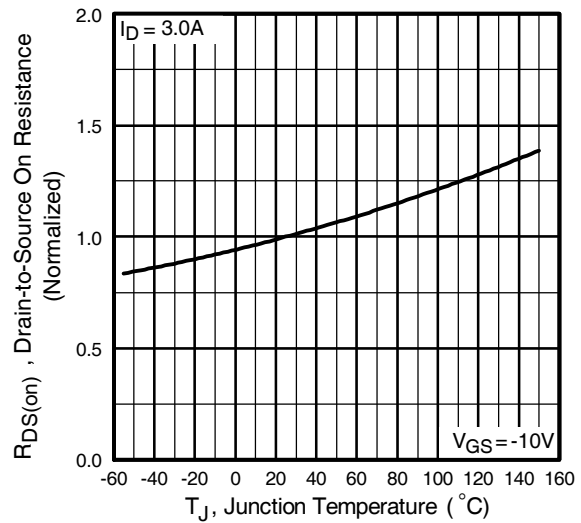


Fig 4. Normalized On-Resistance Vs. Temperature

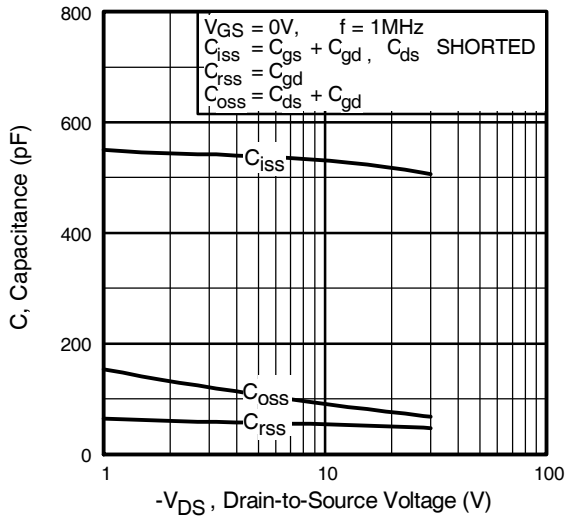


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

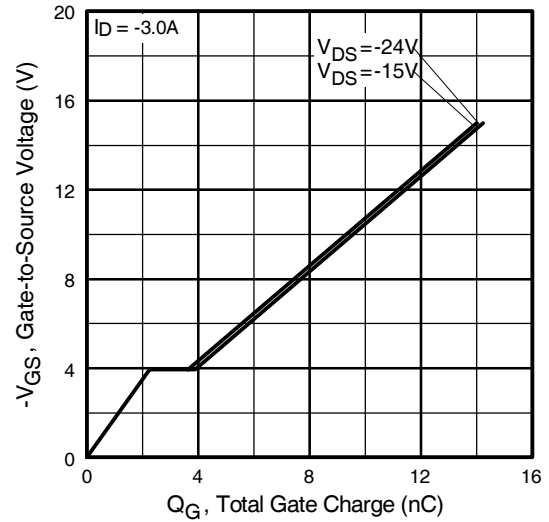


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

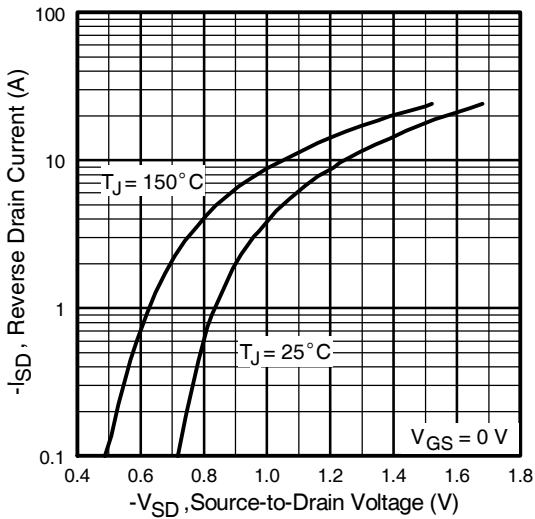


Fig 7. Typical Source-Drain Diode Forward Voltage

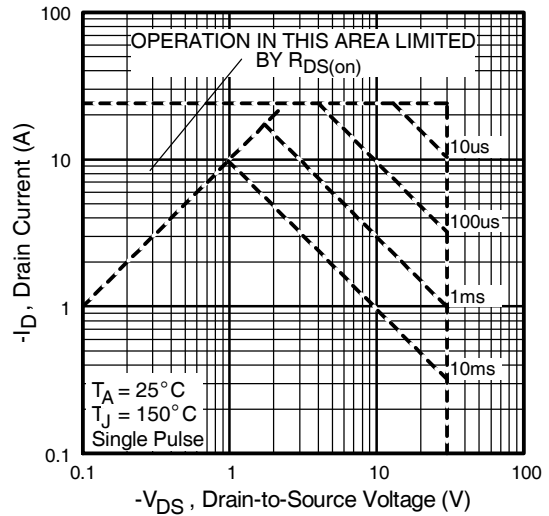


Fig 8. Maximum Safe Operating Area

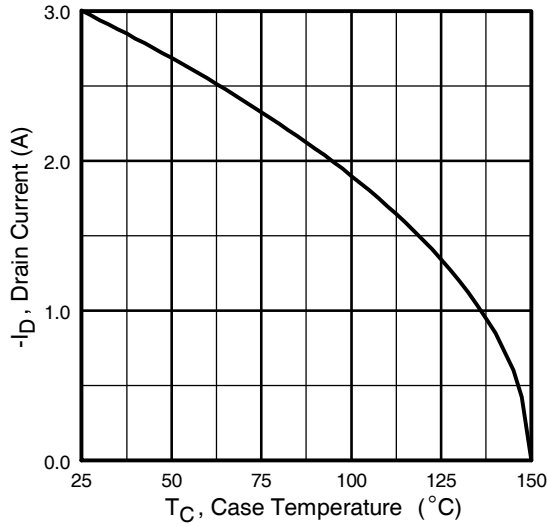


Fig 9. Maximum Drain Current Vs. Case Temperature

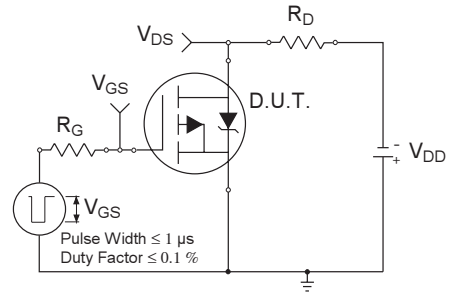


Fig 10a. Switching Time Test Circuit

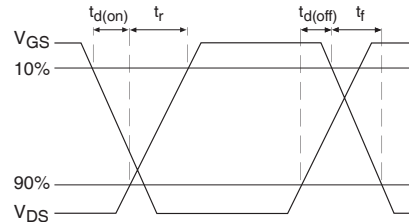


Fig 10b. Switching Time Waveforms

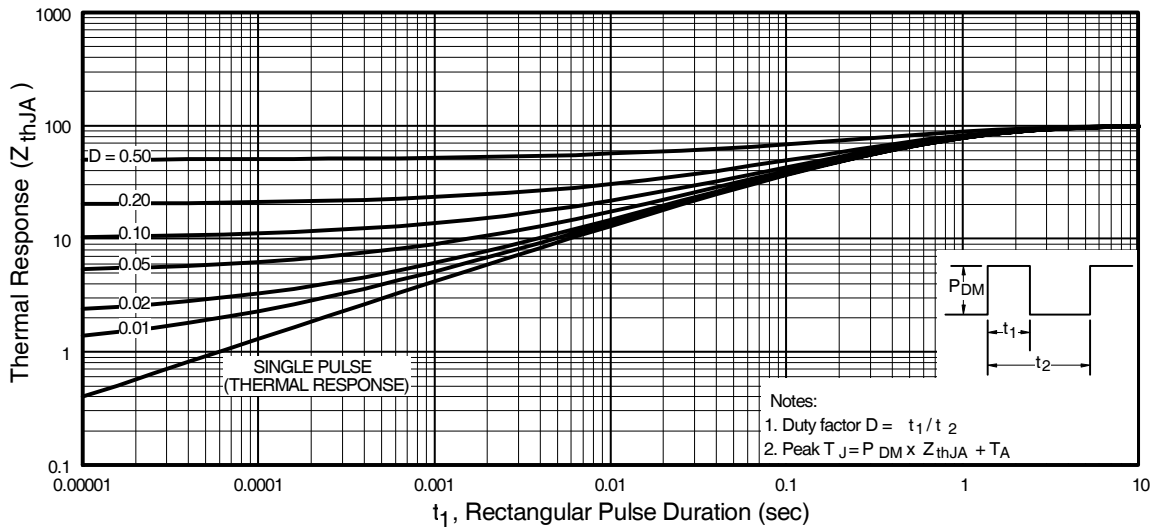


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

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International
IR Rectifier

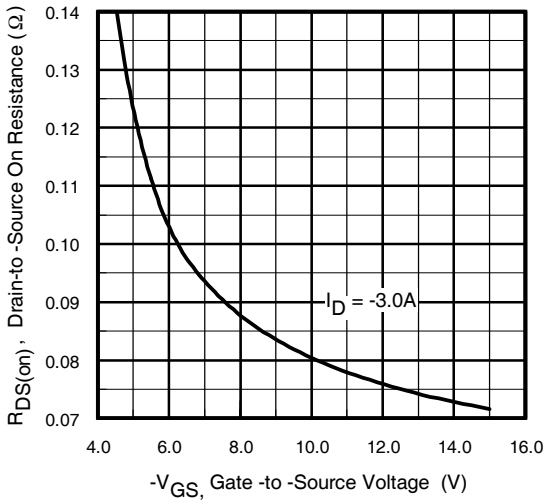


Fig 11. Typical On-Resistance Vs. Gate Voltage

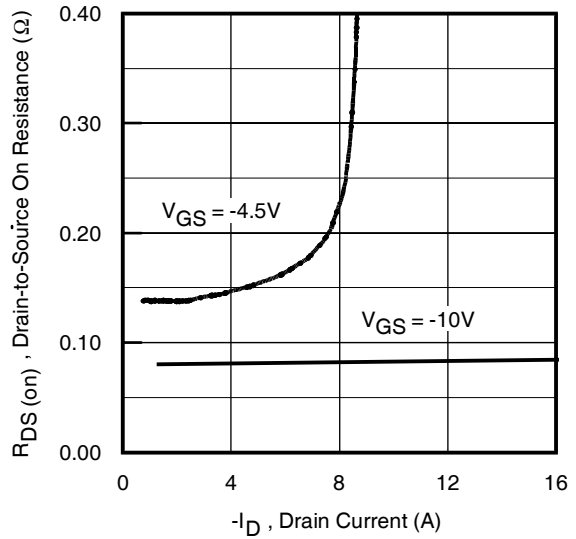


Fig 12. Typical On-Resistance Vs. Drain Current

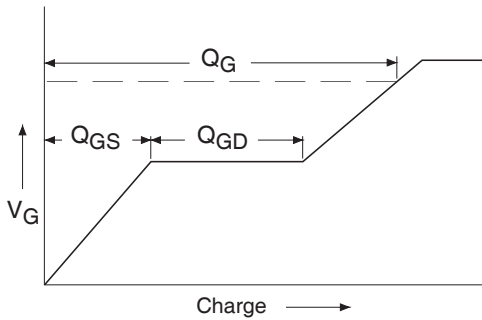


Fig 13a. Basic Gate Charge Waveform

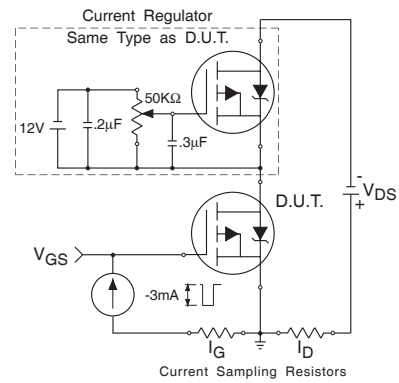


Fig 13b. Gate Charge Test Circuit

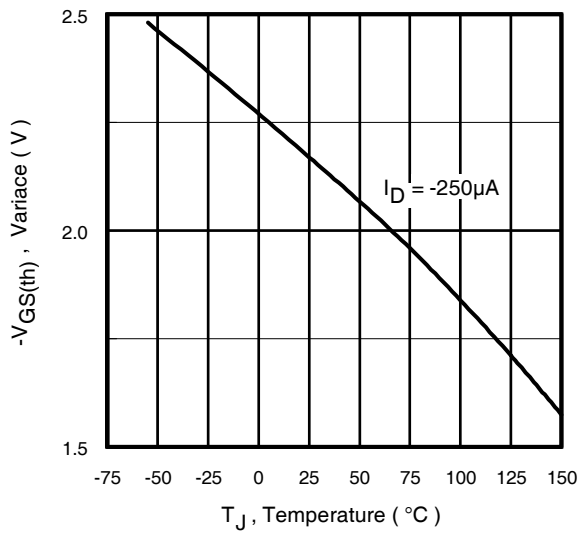


Fig 14. Threshold Voltage Vs. Temperature

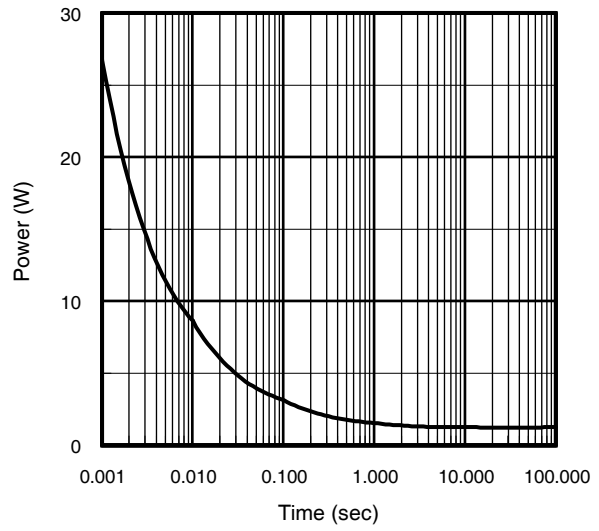
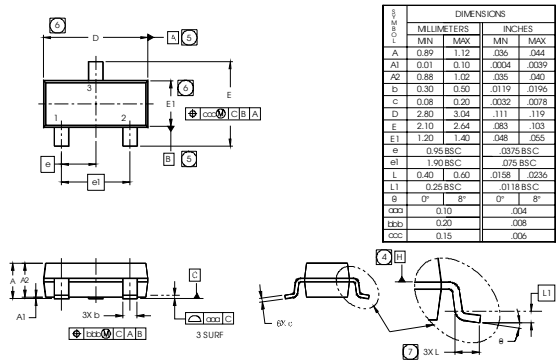


Fig 15. Typical Power Vs. Time

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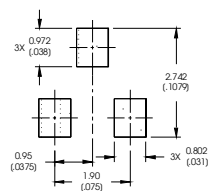
Micro3 (SOT-23) (Lead-Free) Package Outline

Dimensions are shown in millimeters (inches)



DIMENSIONS	DIMENSIONS			
	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	0.89	1.12	.035	.044
A1	0.01	0.10	.0004	.0039
A2	0.88	1.02	.035	.040
D	0.30	0.50	.0119	.0196
C	0.08	0.20	.0032	.0079
D	2.80	3.04	.111	.119
E	2.10	2.64	.083	.103
E1	1.20	1.40	.048	.055
e	0.96 BSC		.0375 BSC	
es	1.90 BSC		.075 BSC	
L	0.40	0.60	.0158	.0236
L1	0.25 BSC		.0118 BSC	
g	0°	8°	0°	8°
gax	0.10		.004	
hax	0.20		.008	
gax	0.15		.006	

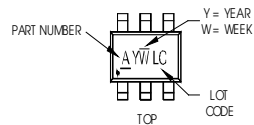
RECOMMENDED FOOTPRINT



- NOTES
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994.
 2. DIMENSIONS ARE SHOWN IN MILLIMETERS AND INCHES.
 3. CONTROLLING DIMENSION: MILLIMETER.
 4. DATUM PLANE H IS LOCATED AT THE MOLD PARTING LINE.
 5. DATUM A AND B TO BE DETERMINED AT DATUM PLANE H.
 6. DIMENSIONS D AND E1 ARE MEASURED AT DATUM PLANE H.
 7. DIMENSION L IS THE LEAD LENGTH FOR SOLDERING TO A SUBSTRATE.
 8. OUTLINE CONFORMS TO JEDEC OUTLINE 1 TO 23A/B.

Micro3 (SOT-23) (Lead-Free) Part Marking Information

W = (1-26) IF PRECEDED BY LAST DIGIT OF CALENDAR YEAR



PART NUMBER CODE REFERENCE:

- A = IRLMS1902
- B = IRLMS1503
- C = IRLMS6702
- D = IRLMS5703
- E = IRLMS6802
- F = IRLMS4502
- G = IRLMS2002
- H = IRLMS6803

Note: A line above the work week (as shown here) indicates Lead-Free.

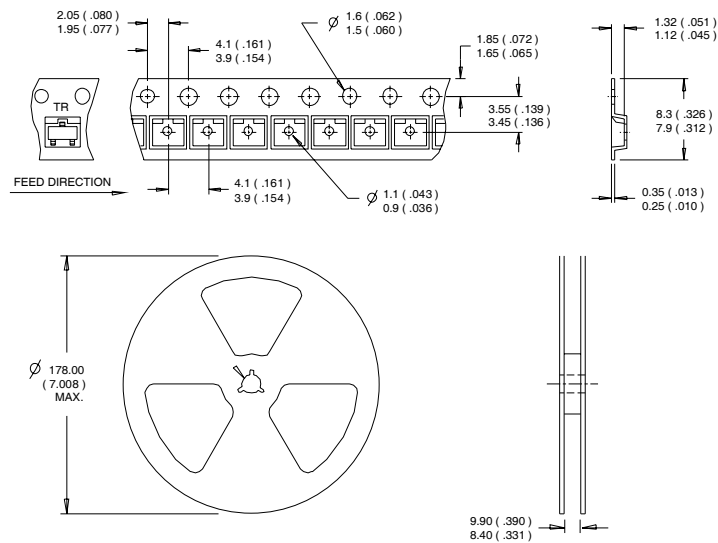
YEAR	Y	WORK WEEK	W
2001	1	01	A
2002	2	02	B
2003	3	03	C
2004	4	04	D
2005	5		
1996	6		
1997	7		
1998	8		
1999	9		
2000	0	24	X
		25	Y
		26	Z

W = (27-52) IF PRECEDED BY A LETTER

YEAR	Y	WORK WEEK	W
2001	A	27	A
2002	B	28	B
2003	C	29	C
2004	D	30	D
2005	E		
1996	F		
1997	G		
1998	H		
1999	J		
2000	K	50	X
		51	Y
		52	Z

Micro3™ Tape & Reel Information

Dimensions are shown in millimeters (inches)



- NOTES:
 1. CONTROLLING DIMENSION : MILLIMETER.
 2. OUTLINE CONFORMS TO EIA-481 & EIA-541.

Data and specifications subject to change without notice.